

■ Description

HWET05012B is a low - capacitance Transient Voltage Suppressor (TVS) designed to provide electrostatic discharge (ESD) protection for data, control or power lines.

With typical capacitance of 12pF only, HWET05012B is designed to protect parasitic – sensitive systems against over-voltage and over-current transient events. It complies with IEC 61000-4-2 (ESD), Level 4 ($\pm 15\text{kV}$ air, $\pm 8\text{kV}$ contact discharge), IEC 61000-4-4 (electrical fast transient - EFT) (40A, 5/50 ns), very fast charged device model (CDM) ESD and cable discharge event (CDE), etc. HWET05012B uses ultra - small uDFN-2L package. Each HWET05012B device can protect one data line. It offers system designers flexibility to protect single data line where space is a premium concern.

■ Mechanical Characteristics

- uDFN-2L package
- Flammability Rating: UL 94V-0
- Marking: Part number, date code
- Packaging: Tape and Reel

■ Circuit Diagram



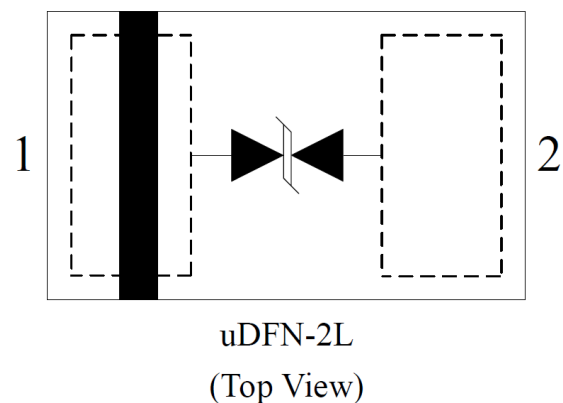
■ Features

- Transient protection for high-speed data lines IEC 61000-4-2 (ESD) $\pm 30\text{kV}$ (Air) $\pm 30\text{kV}$ (Contact)
- IEC 61000-4-4 (EFT) 40A (5/50 ns)
- Cable Discharge Event (CDE)
- Package optimized for high-speed lines
- Ultra-small package (1.0mm*0.6mm*0.55mm)
- Protects one data, control or power line
- Low capacitance: 12pF (Typical)
- Low leakage current: $0.1\mu\text{A}$ @ VRWM (Typ.)
- Low clamping voltage
- Each I/O pin can withstand over 1000 ESD strikes for $\pm 8\text{kV}$ contact discharge
- ROHS compliant

■ Applications

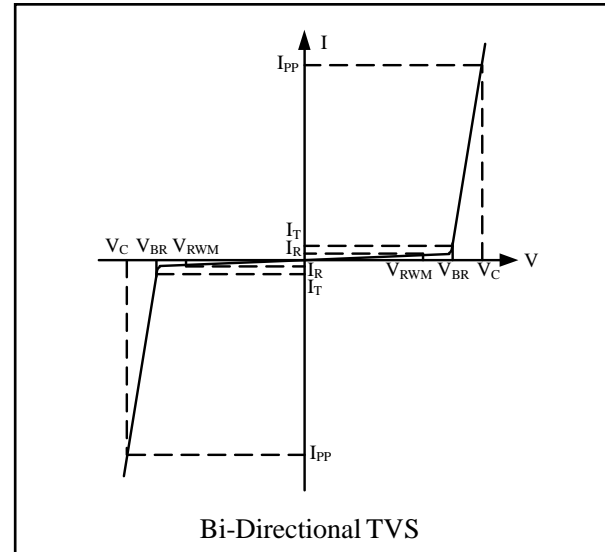
- Portable Electronics
- Desktops, Servers and Notebooks
- Cellular Phones
- MP3 Ports
- Digital Camera Ports
- Subscriber Identity Module (SIM) card

■ Pin Configuration



Electrical characteristics (Ta = 25 °C)

Symbol	Parameter
V_{RWM}	Nominal Reverse Working Voltage
I_R	Reverse Leakage Current @ V_{RWM}
V_{BR}	Reverse Breakdown Voltage @ I_T
I_T	Test Current for Reverse Breakdown
V_C	Clamping Voltage @ I_{PP}
I_{PP}	Maximum Peak Pulse Current
C_{ESD}	Parasitic Capacitance
V_R	Reverse Voltage
f	Small Signal Frequency



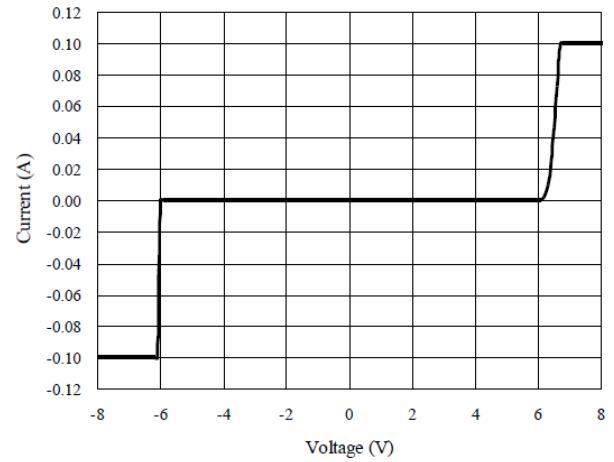
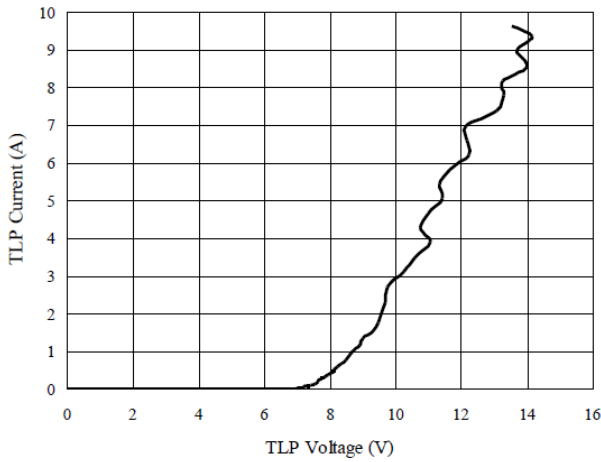
Symbol	Test Condition	Minimum	Typical	Maximum	Units
V_{RWM}				5	V
I_R	$V_{RWM} = 5V, T = 25^{\circ}C$ Between I/O_1 and I/O_2		0.1	1	μA
V_{BR}	$I_T = 1mA$ Between I/O_1 and I/O_2	5.5	6.0	8.0	V
V_C	$I_{PP} = 1A, t_p = 8/20\mu s$ Between I/O_1 and I/O_2			9	V
V_C	$I_{PP} = 4A, t_p = 8/20\mu s$ Between I/O_1 and I/O_2			12	V
C_{ESD}	$V_R = 0V, f = 1MHz$ Between I/O_1 and I/O_2		12	15	pF

Absolute Maximum Rating

Symbol	Parameter	Value	Units
P_{PP}	Peak Pulse Power (8/20 μs)	48	W
I_{PP}	Peak Pulse Current($t_p=8/20\mu s$)	4	A
V_{ESD}	ESD per IEC 61000-4-2(Air)	± 30	kV
	ESD per IEC 61000-4-2 (Contact)	± 30	
T_{OPT}	Operating Temperature	-55/+125	$^{\circ}C$
T_{STG}	Storage Temperature	-55/+150	$^{\circ}C$

TLP Measurement of I/O_1 to I/O_2

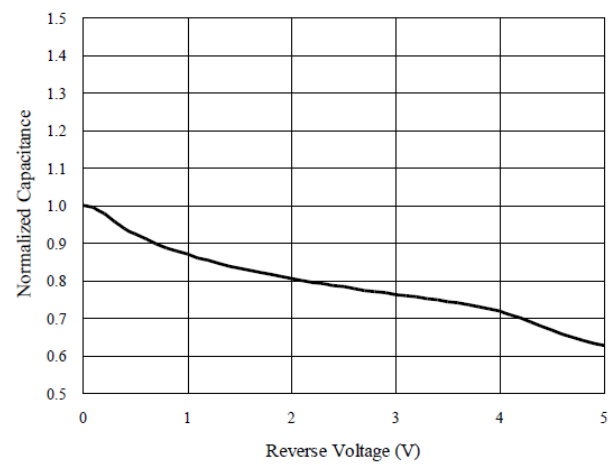
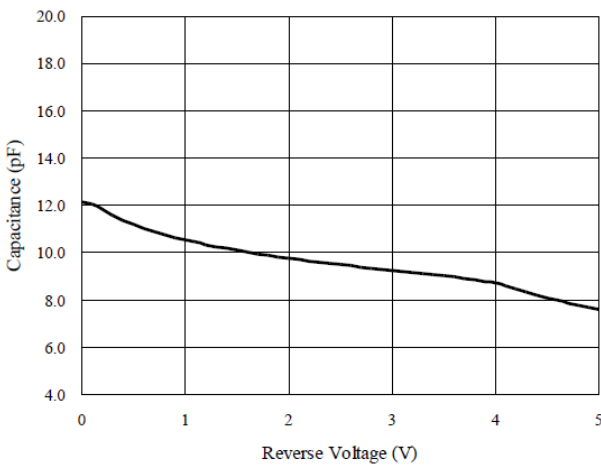
Voltage Sweeping of I/O_1 to I/O_2



Capacitance vs. Voltage of I/O_1 to I/O_2 (f = 1MHz)

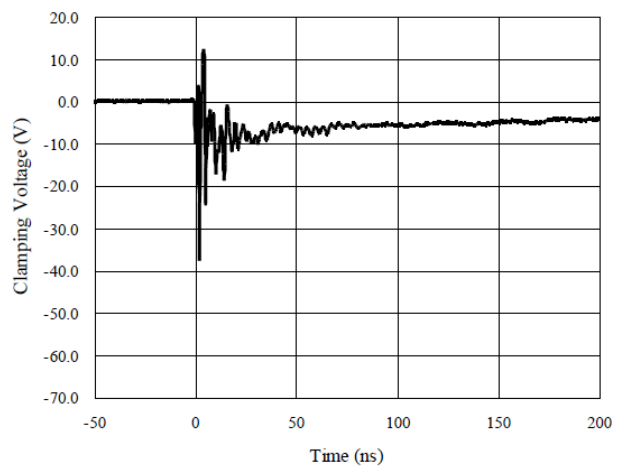
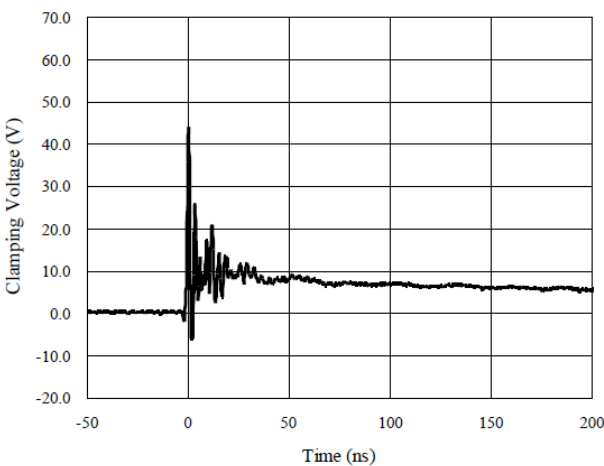
Capacitance vs. Reverse Voltage

Normalized Capacitance vs. Reverse Voltage



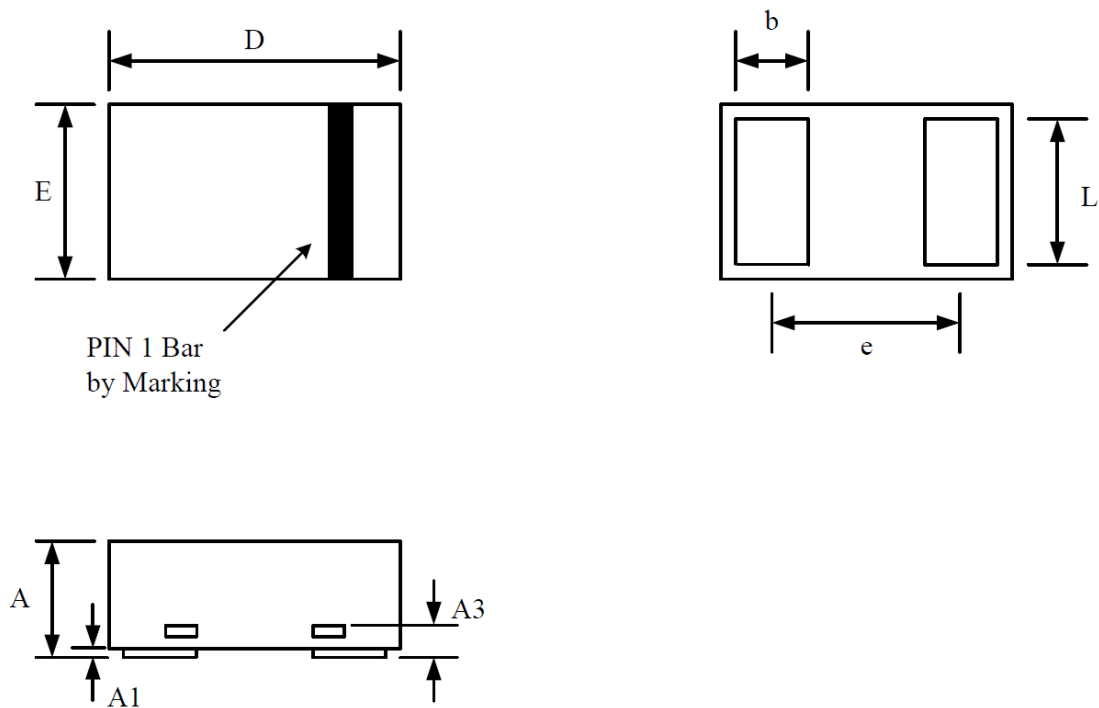
ESD Clamping of I/O_1 to I/O_2 (+8kV Contact per IEC 61000-4-2)

ESD Clamping of I/O_1 to I/O_2 (-8kV Contact per IEC 61000-4-2)



Package Outline

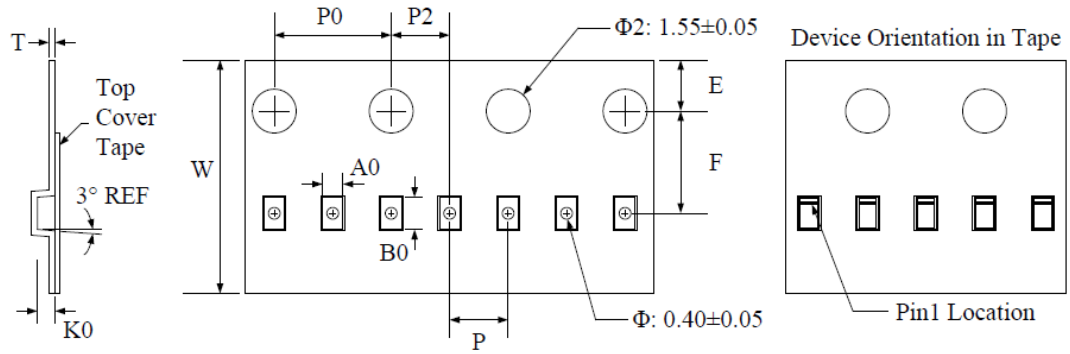
- uDFN-2L package
- 2 leads, very small package
- MSL-1



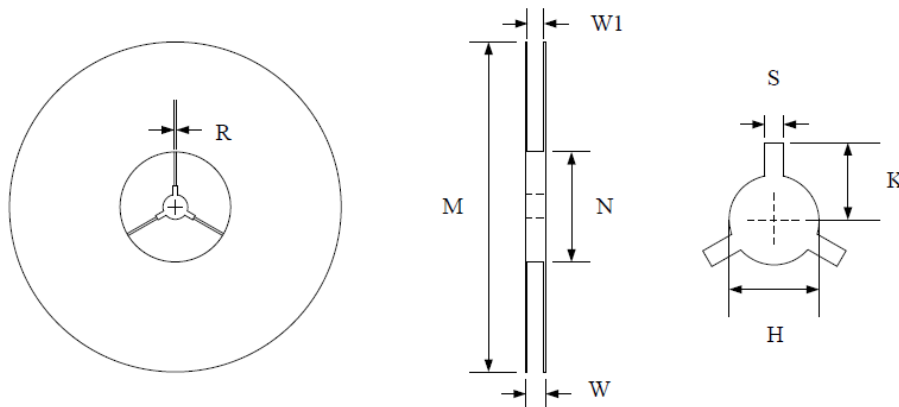
Package Dimensions (Controlling dimensions are in millimeters)

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Minimum	Maximum	Minimum	Maximum
A	0.400	0.550	0.016	0.022
A1	0.000	0.050	0.000	0.002
A3	0.125 REF		0.005 REF	
D	0.950	1.050	0.037	0.041
E	0.550	0.650	0.022	0.026
b	0.200	0.300	0.008	0.012
e	0.650 BSC		0.026 BSC	
L	0.450	0.550	0.018	0.022

Tape and Reel Specification



Symbol	W	A0	B0	K0	E	F	P	P0	P2	T
Dimensions (mm)	8.00±0.1	0.7±0.05	1.15±0.05	0.55±0.05	1.75±0.1	3.5±0.05	2.0±0.1	4.0±0.1	2.0±0.05	0.2±0.05



Symbol	Reel Size	M	N	W	W1	H	S	K	R
Dimensions (mm)	Φ178	178.0±1.0	60.0±1.0	11.5±0.5	9.0±0.5	13.0±0.5	2.0±0.1	11.0±0.2	1.0±0.05